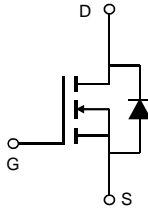


General Description

The AON2400 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

V_{DS}	8V
I_D (at $V_{GS}=4.5V$)	8A
$R_{DS(ON)}$ (at $V_{GS} = 2.5V$)	< 11m Ω
$R_{DS(ON)}$ (at $V_{GS} = 1.8V$)	< 13m Ω
$R_{DS(ON)}$ (at $V_{GS} = 1.5V$)	< 16m Ω
$R_{DS(ON)}$ (at $V_{GS} = 1.2V$)	< 23m Ω



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	8	V
Gate-Source Voltage	V_{GS}	± 5	V
Continuous Drain Current ^G	I_D	$T_A=25^\circ\text{C}$	8
		$T_A=100^\circ\text{C}$	6
Pulsed Drain Current ^C	I_{DM}	32	A
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	2.8
		$T_A=70^\circ\text{C}$	1.8
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	37	45	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient ^{A,D}		Steady-State	66	80

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	8			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =8V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±5V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA		0.46		V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	32			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =2.5V, I _D =8A T _J =125°C		8.5 11	11 14	mΩ
		V _{GS} =1.8V, I _D =6A		10	13	
		V _{GS} =1.5V, I _D =5A		11.5	16	
		V _{GS} =1.2V, I _D =3A		16	23	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =8A		100		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.53	1	V
I _S	Maximum Body-Diode Continuous Current				4.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =4V, f=1MHz		1645		pF
C _{oss}	Output Capacitance			470		pF
C _{rss}	Reverse Transfer Capacitance			320		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.6	3.2	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =4V, I _D =8A		16		nC
Q _{gs}	Gate Source Charge			2		nC
Q _{gd}	Gate Drain Charge			2.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =4.5V, V _{DS} =4V, R _L =0.5Ω, R _{GEN} =3Ω		7		ns
t _r	Turn-On Rise Time			25		ns
t _{D(off)}	Turn-Off DelayTime			37		ns
t _f	Turn-Off Fall Time			13		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =8A, di/dt=100A/μs		17		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =8A, di/dt=100A/μs		9		nC

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t ≤ 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

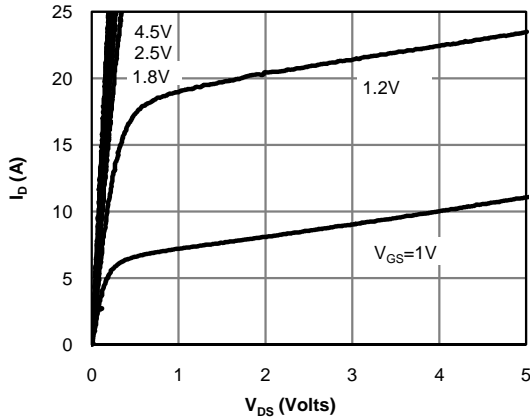


Fig 1: On-Region Characteristics (Note E)

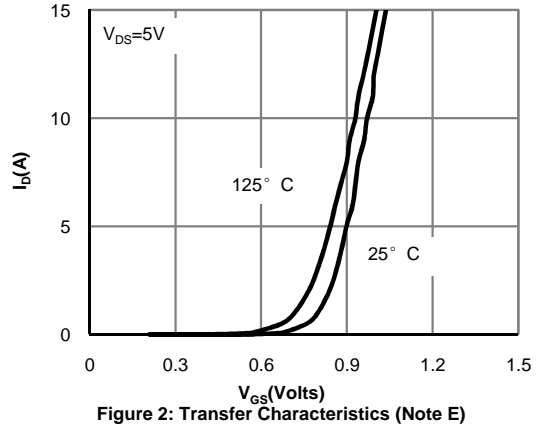


Figure 2: Transfer Characteristics (Note E)

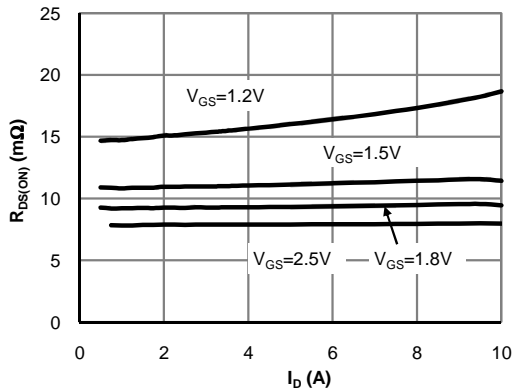


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

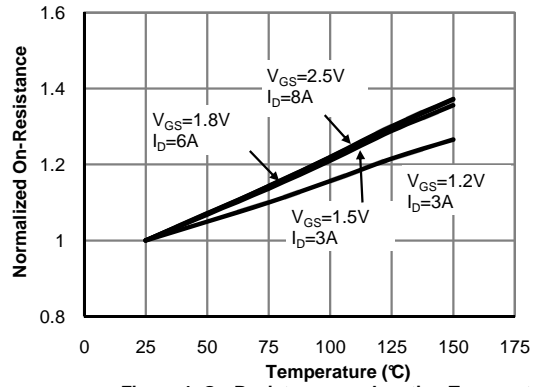


Figure 4: On-Resistance vs. Junction Temperature (Note E)

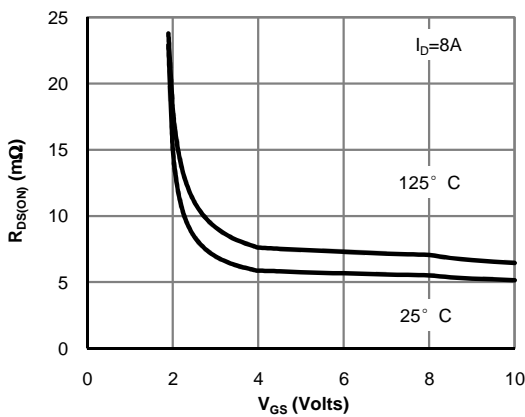


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

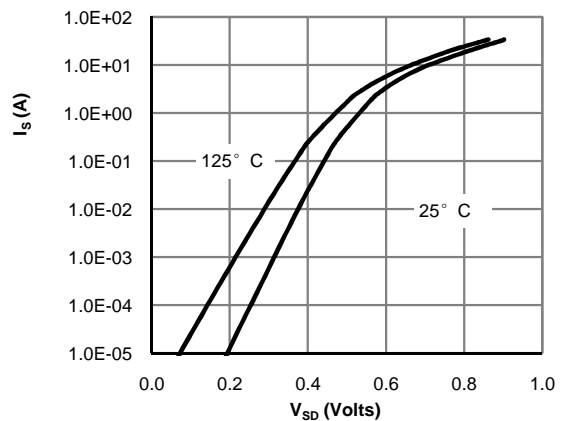


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

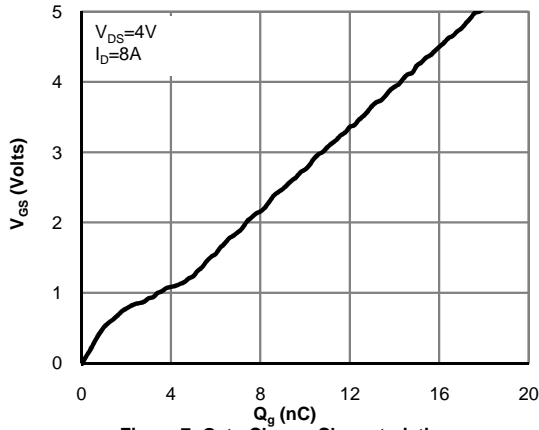


Figure 7: Gate-Charge Characteristics

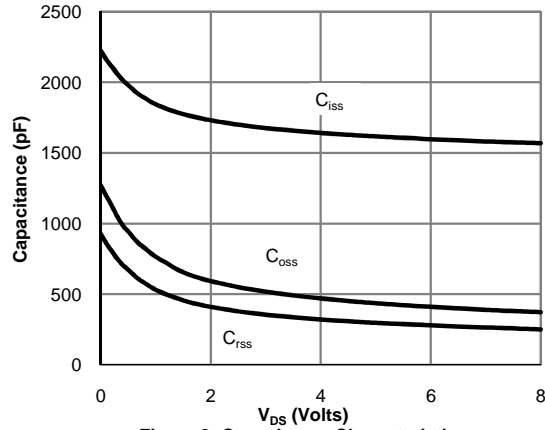


Figure 8: Capacitance Characteristics

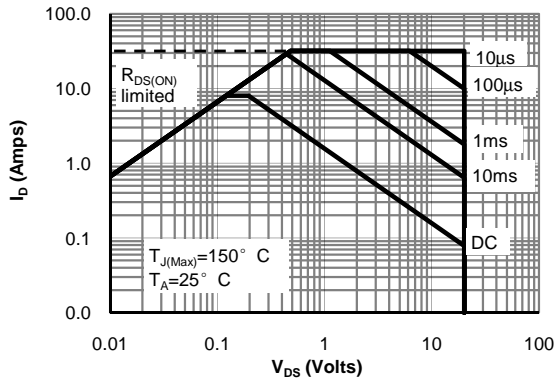


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

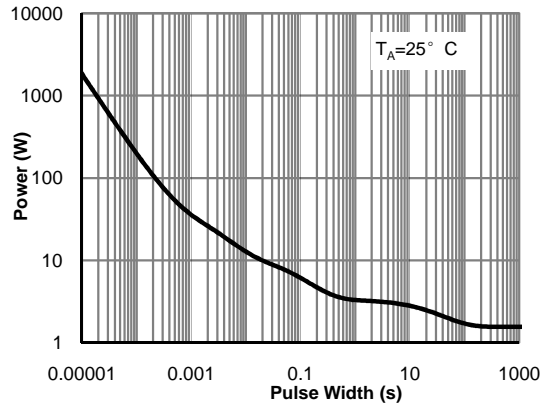


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note H)

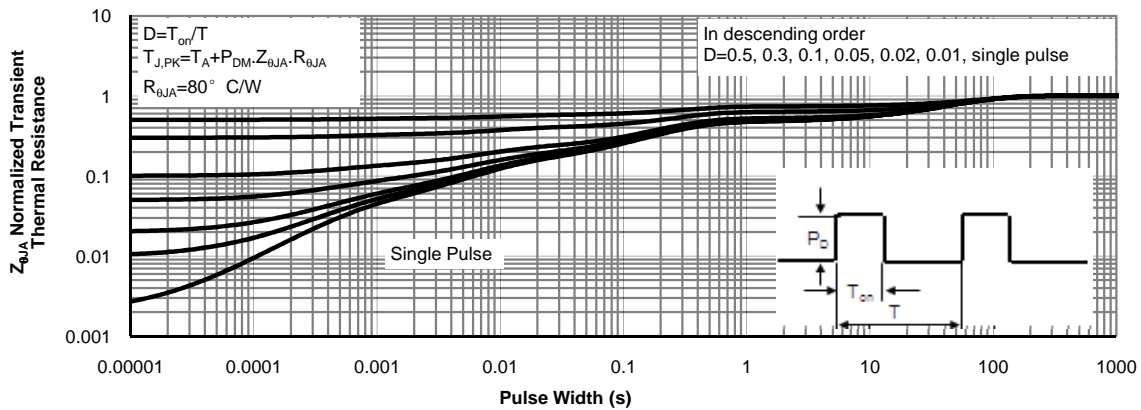
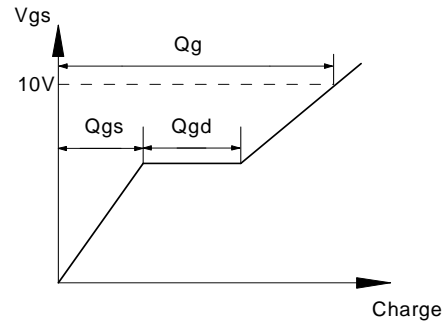
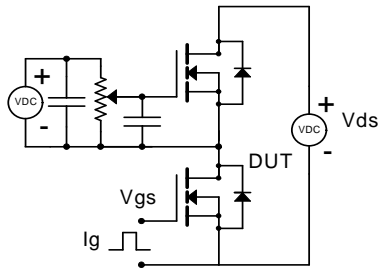
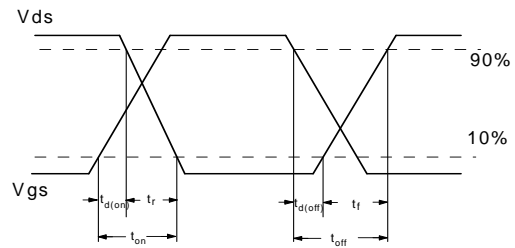
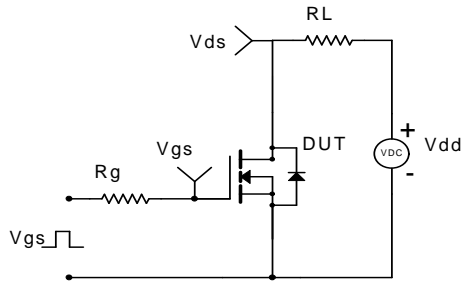


Figure 12: Normalized Maximum Transient Thermal Impedance (Note H)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

